

# **Quad 2-Channel Multiplexer** with 3-State Outputs

### **MC74LVX257**

The MC74LVX257 is an advanced high speed CMOS quad 2-channel multiplexer fabricated with silicon gate CMOS technology.

It consists of four 2-input digital multiplexers with common select (S) and enable  $(\overline{OE})$  inputs. When  $(\overline{OE})$  is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

The inputs tolerate voltages up to 5.5 V, allowing the interface of 5.0 V systems to 3.0 V systems.

#### **Features**

- High Speed:  $t_{PD} = 4.5 \text{ ns}$  (Typ) at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25 \, ^{\circ}C$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 100 mA
- Chip Complexity: FETs = 100; Equivalent Gates = 25
- ESD Performance:

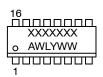
Human Body Model > 2000 V;

• These Devices are Pb-Free and are RoHS Compliant

#### MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



XXXXXXX = Specific Device Code

A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

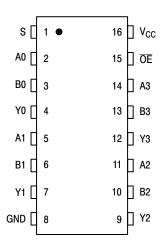


Figure 1. Pin Assignment

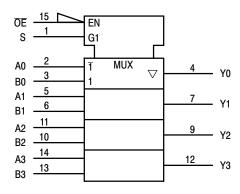


Figure 3. IEC Logic Symbol

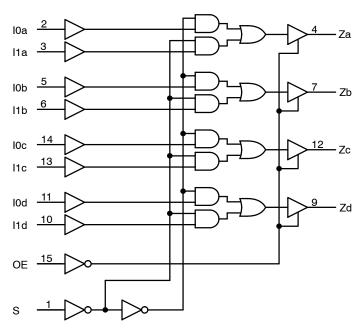


Figure 2. Expanded Logic Diagram

#### **FUNCTION TABLE**

Inp	Outputs		
ŌĒ	s	Y0 - Y3	
Н	Х	Z	
L	L	A0-A3	
L	Н	B0 – B3	

A0 - A3, B0 - B3 = the levels of the respective Data-Word Inputs.

#### **MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit	
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +6.5	V	
V <sub>IN</sub>	DC Input Voltage		-0.5 to +6.5	V	
V <sub>OUT</sub>	DC Output Voltage		-0.5 to V <sub>CC</sub> +0.5	V	
I <sub>IN</sub>	DC Input Current, per Pin		±20	mA	
I <sub>OUT</sub>	DC Output Current, Per Pin		±25	mA	
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins		±75	mA	
I <sub>IK</sub>	Input Clamp Current		-20	mA	
lok	Output Clamp Current		±20	mA	
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C	
TL	Lead Temperature, 1 mm from Case for 10 secs		260	°C	
TJ	Junction Temperature Under Bias		+150	°C	
$\theta_{\sf JA}$	Thermal Resistance (Note 1)	SOIC-16	126	°C/W	
		TSSOP-16	159		
P <sub>D</sub>	Power Dissipation in Still Air at 25 °C	SOIC-16	995	mW	
		TSSOP-16	787		
MSL	Moisture Sensitivity		Level 1	-	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-	
V <sub>ESD</sub>	ESD Withstand Voltage (Note 2)	Human Body Model Charged Device Model	2000 N/A	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
   HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	3.6	V
V <sub>IN</sub>	DC Input Voltage	0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, all Package Types	-40	85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time $V_{CC} = 3.3 \text{ V} \pm 0.3$	V 0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### DC CHARACTERISTICS (Voltages Referenced to GND)

			V <sub>CC</sub>	1	A = 25 °	С	-40 °C ≤	T <sub>A</sub> ≤ 85 °C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 3.6	0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub> 0.7 V <sub>CC</sub>			0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub> 0.7 V <sub>CC</sub>		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 3.6			0.25 V <sub>CC</sub> 0.3 V <sub>CC</sub> 0.3 V <sub>CC</sub>		0.25 V <sub>CC</sub> 0.3 V <sub>CC</sub> 0.3 V <sub>CC</sub>	V
V <sub>OH</sub>	High-Level Output Voltage	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \text{ mA}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V <sub>OL</sub>	Low-Level Output Voltage	$I_{OL} = 50 \ \mu A$ $I_{OL} = 50 \ \mu A$ $I_{OL} = 4 \ mA$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l <sub>OZ</sub>	Maximum 3-State Leakage Current	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND	3.6			±0.1		±1.0	μА
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 3.6			±0.1		±1.0	μА
Icc	Maximum Quiescent Supply Current (per package)	V <sub>IN</sub> = V <sub>CC</sub> or GND	3.6	1.0	1.0	2.0		40	μΑ

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0 \text{ ns}$

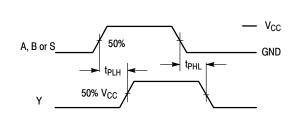
				Γ <sub>A</sub> = 25 °(	C	-40 °C ≤ 7	Γ <sub>A</sub> ≤ 85 °C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A or B to Y	$V_{CC}$ = 2.7 V $C_L$ = 15 pF $C_L$ = 50 pF		6.5 9.5	10.0 14.0	1.0 1.0	15.0 18.5	ns
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} \text{ C}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$		4.5 7.5	8.0 12.0	1.0 1.0	10.0 13.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, S to Y	$V_{CC} = 2.7 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		8.0 10.5	12.0 15.5	1.0 1.0	17.0 20.0	ns
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} \text{ C}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$		6.0 8.5	10.0 13.5	1.0 1.0	12.0 15.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Output Enable, Time, OE to Y	$\begin{array}{ll} V_{CC} = 2.7 \ V & C_L = 15 \ pF \\ R_L = 1 \ k\Omega & C_L = 50 \ pF \end{array}$		7.5 10.5	11.5 15.0	1.0 1.0	16.5 18.0	ns
		$\begin{aligned} &V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} \text{ C}_{L} = 15 \text{ pF} \\ &R_{L} = 1 \text{ k}\Omega & C_{L} = 50 \text{ pF} \end{aligned}$		5.5 8.5	9.5 13.0	1.0 1.0	11.5 15.0	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Output Disable, Time, OE to Y	$\begin{array}{ll} V_{CC} = 2.7 & C_L = 50 \text{ pF} \\ R_L = 1 \text{ k}\Omega & \end{array}$		13.0	17.0	1.0	18.0	ns
		$V_{CC}$ = 3.3 V ± 0.3 V $C_L$ = 50 pF $R_L$ = 1 k $\Omega$		12	17.0	1.0	18.0	
C <sub>IN</sub>	Maximum Input Capacitance			4	10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 3.3 V	
$C_{PD}$	Power Dissipation Capacitance (Note 3)	20	pF

<sup>3.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

#### NOISE CHARACTERISTICS Input $t_r$ = $t_f$ = 3.0 ns, $C_L$ = 50 pF, $V_{CC}$ = 3.3 V

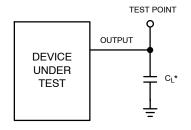
		T <sub>A</sub> = 25 °C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.5	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.5	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

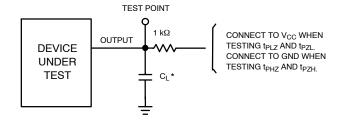


 $V_{CC}$ 0E 50% GND ← t<sub>PZL</sub> t<sub>PLZ</sub>→ HIGH **IMPEDANCE** 50% V<sub>CC</sub>  $V_{OL} + 0.3V$  $t_{PZH}$ t<sub>PHZ</sub>→ V<sub>OH</sub> - 0.3V 50% V<sub>CC</sub> HIGH **IMPEDANCE** 

Figure 4. Switching Waveform

Figure 5. Switching Waveform





\* Includes all probe and jig capacitance

\* Includes all probe and jig capacitance

Figure 6. Test Circuit

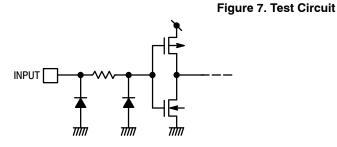


Figure 8. Input Equivalent Circuit

#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
MC74LVX257DTR2G	LVX 257	TSSOP-16	2500 / Tape & Reel
MC74LVX257DR2G	LVX257G	SOIC-16	2500 / Tape & Reel

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

#### **REVISION HISTORY**

Revision	Description of Changes	Date
6	Modified voltage ratings from 7.0 V to 6.5 V. Rebranded the Data Sheet to <b>onsemi</b> format.	07/09/2025



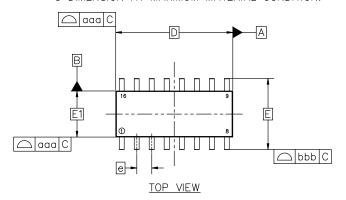


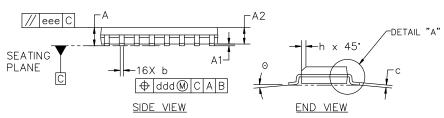
#### SOIC-16 9.90x3.90x1.37 1.27P CASE 751B ISSUE M

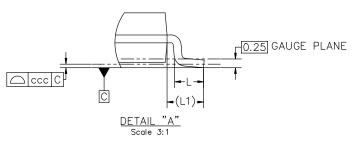
**DATE 18 OCT 2024** 

#### NOTES:

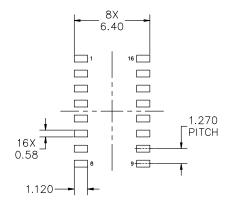
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- 5. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







MILLIMETERS						
DIM	MIN	MAX				
А	1.35	1.55	1.75			
A1	0.10	0.18	0.25			
A2	1.25	1.37	1.50			
b	0.35	0.42	0.49			
С	0.19	0.22	0.25			
D	9.90 BSC					
E		6.00 BSC				
E1		3.90 BSC				
е		1.27 BSC				
h	0.25		0.50			
L	0.40	0.83	1.25			
L1		1.05 REF				
Θ	0.		7*			
TOLERAN	CE OF FC	RM AND	POSITION			
aaa		0.10				
bbb		0.20				
ccc		0.10				
ddd		0.25				
eee		0.10				



#### RECOMMENDED MOUNTING FOOTPRINT

\*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERRM/D

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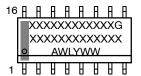
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#### **SOIC-16 9.90x3.90x1.37 1.27P** CASE 751B

ISSUE M

**DATE 18 OCT 2024** 

## GENERIC MARKING DIAGRAM\*



XXXXX = Specific Device Code

A = Assembly Location
WL = Wafer Lot

Y = Year
WW = Work Week
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:		STYLE 3:	S	TYLE 4:	
	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
	BASE	2.	ANODE	2.	BASE. #1	2.	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER. #1	3.	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	
	EMITTER	12.	CATHODE	12.		12.	
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH		
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT)		
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT)		
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH		
5.	DRAIN, #3	5.		5.	COMMON DRAIN (OUTPUT)		
6.	DRAIN, #3	6.		6.	COMMON DRAIN (OUTPUT)		
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPUT)		
0							
8.	DRAIN, #4		CATHODE	8.	SOURCE P-CH		
	GATE, #4	9.	ANODE	9.	SOURCE P-CH		
9. 10.	GATE, #4 SOURCE, #4	9. 10.	ANODE ANODE	9. 10.	SOURCE P-CH COMMON DRAIN (OUTPUT)		
9. 10. 11.	GATE, #4 SOURCE, #4 GATE, #3	9. 10. 11.	ANODE ANODE ANODE	9. 10. 11.	SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
9. 10. 11. 12.	GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3	9. 10. 11. 12.	ANODE ANODE ANODE ANODE	9. 10. 11. 12.	SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
9. 10. 11. 12. 13.	GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	9. 10. 11. 12. 13.	ANODE ANODE ANODE ANODE ANODE	9. 10. 11. 12. 13.	SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH		
9. 10. 11. 12. 13. 14.	GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2	9. 10. 11. 12. 13. 14.	ANODE ANODE ANODE ANODE ANODE ANODE	9. 10. 11. 12. 13.	SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT)		
9. 10. 11. 12. 13. 14.	GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1	9. 10. 11. 12. 13. 14.	ANODE ANODE ANODE ANODE ANODE ANODE ANODE	9. 10. 11. 12. 13. 14.	SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
9. 10. 11. 12. 13. 14.	GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2	9. 10. 11. 12. 13. 14.	ANODE ANODE ANODE ANODE ANODE ANODE	9. 10. 11. 12. 13.	SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT)		

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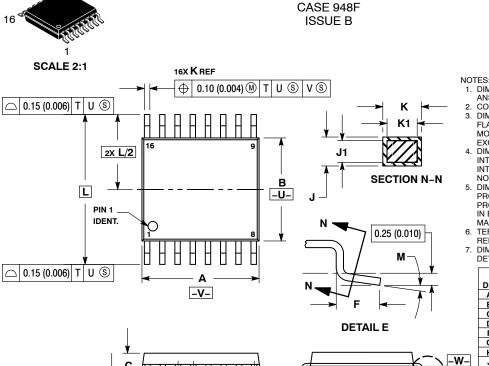
**DATE 19 OCT 2006** 



☐ 0.10 (0.004)

SEATING PLANE

D

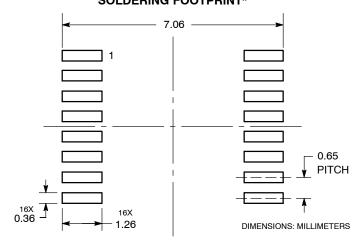


TSSOP-16 WB

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL
- IN TERLEAD FLASH OH PROTHOSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0 °	8°	0°	8 °

#### **RECOMMENDED** SOLDERING FOOTPRINT\*



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC** MARKING DIAGRAM\*



XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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**DETAIL E** 

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